

/ Descriptions

Silicon NPN transistor in a SOT-23 Plastic Package.

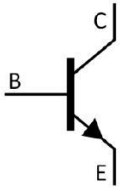
/ Features

High h_{FE} , complementary pair with 2SA1981S.

/ Applications

Audio power amplifier application.

/ Pin Configuration



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ Electrical Characteristics

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HFAO	HFAY

/ Absolute Maximum Ratings (T₂₅)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CBO}	35	V
Collector to Emitter Voltage	V _{CEO}	30	V
Emitter to Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	800	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

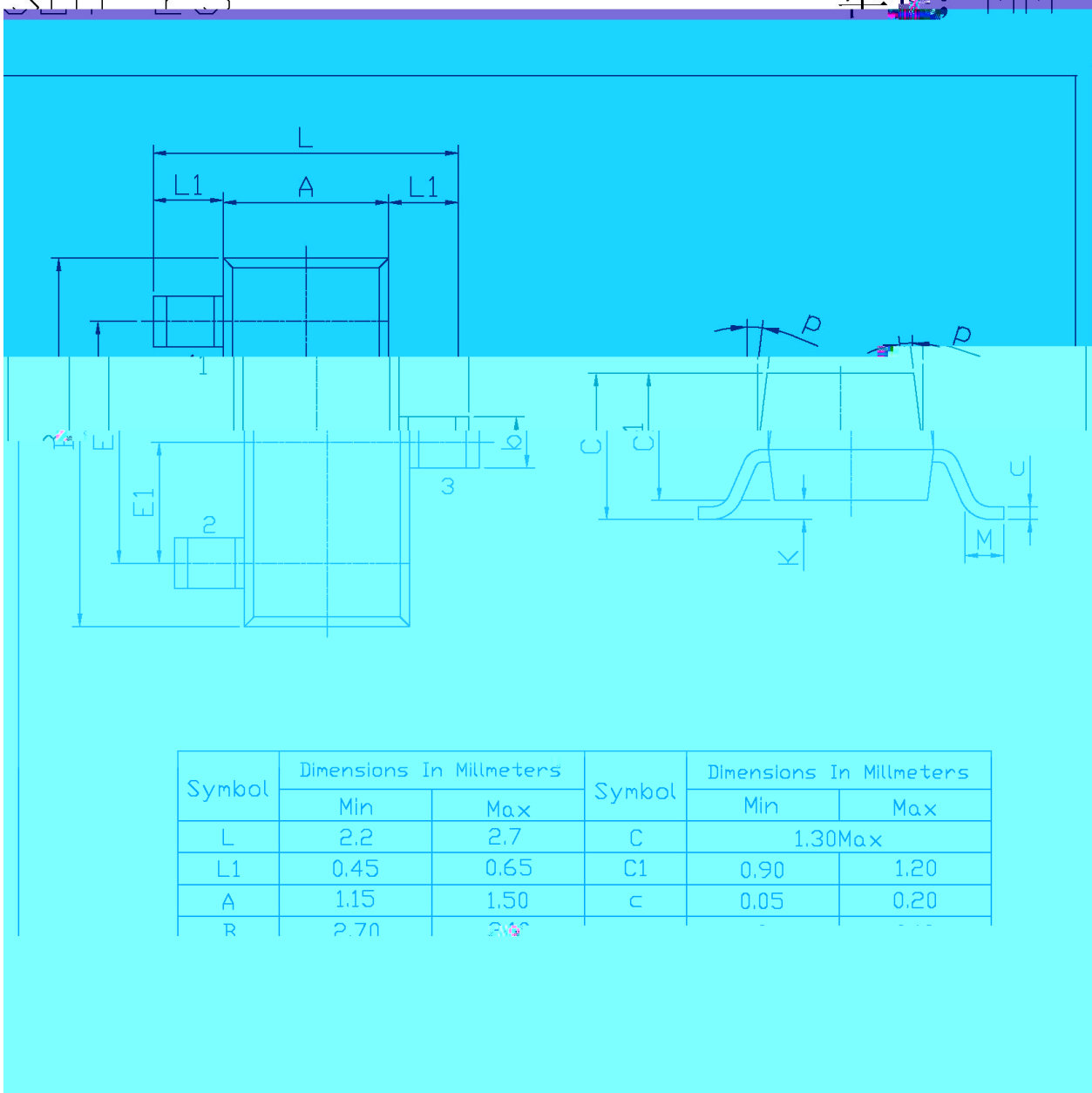
/ Electrical Characteristics (T₂₅)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V _{CBO}	I _C =100μA I _E =0	35			V
Collector to Emitter Breakdown Voltage	V _{CEO}	I _C =1.0mA I _B =0	30			V
Emitter to Base Breakdown Voltage	V _{EBO}	I _E =10μA I _C =0	5.0			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =35V I _E =0			0.1	μA
Emitter Base Cut-Off Current	I _{EBO}	V _{EB} =5.0V I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =1.0V I _C =100mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA I _B =50mA			0.5	V
Transition Frequency	f _T	V _{CE} =5.0V I _C =10mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V I _E =0 f=1.0MHz		13		pF

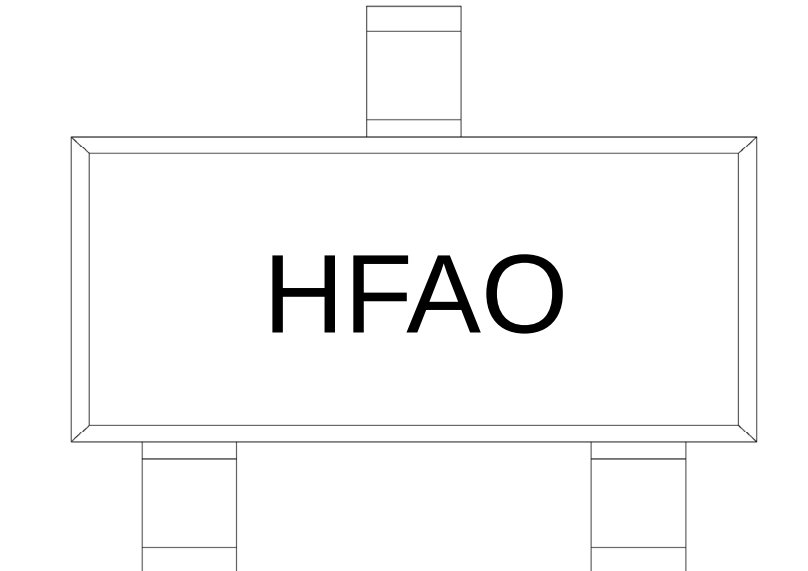
/ Packaging

SOT-23

单位: mm



/ Mingstudio



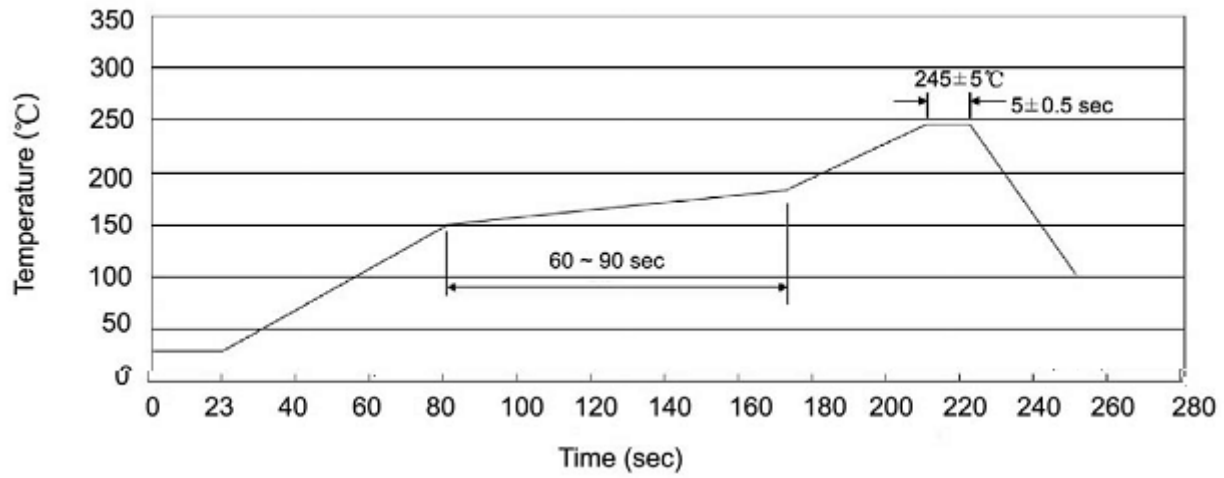
Note:

Company Code

Product Type Code

h_{FE} Classifications Symbol Code

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Note:

1. Preheating: 25~150 , Time: 60~90sec.
2. Peak Temp.: 245±5 , Duration: 5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance Soldering Test Conditions

260±5 10±1 sec. Temp.: 260±5°C Time: 10±1 sec

/ Reel

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		

/ Notes